IN THE CLAIMS:

1. (Currently Amended) An organic EL panel having a plurality of organic EL elements arranged in a matrix, comprising:

a drive transistor provided to each of the plurality of organic EL elements, for controlling a drive current to be supplied to a corresponding organic EL element; and

a peripheral transistor ~~provided near the periphery~~ disposed within a peripheral circuit which is formed outside of a display area where the plurality of organic EL elements are arranged, for outputting a signal for controlling the drive transistor,

wherein a gate length of the drive transistor is set longer than a gate length of the peripheral transistor.

2. (Original) The organic EL panel according to claim 1, wherein

the gate length of the peripheral transistor is set to a value between 1 and 10 μm.

3. (Original) The organic EL panel according to claim 1, wherein

the gate length of the drive transistor is set to a value between 10 and 100 μm.

4. (Original) The organic EL panel according to claim 1, wherein

a gate width of the drive transistor and a gate width of the peripheral transistor are set to the same value.

5. (Currently Amended) An organic EL panel having a plurality of organic EL elements arranged in a matrix, comprising:

a drive transistor provided to each of the plurality of organic EL elements, for controlling a drive current to be supplied to a corresponding organic EL element; and

a peripheral transistor ~~provided near the periphery~~ disposed within a peripheral circuit which is formed outside of a display area where the plurality of organic EL elements are arranged, for outputting a signal for controlling the drive transistor,

wherein (a gate length L)/(a gate width W) of the drive transistor is set larger than (a gate length L)/(a gate width W) of the peripheral transistor.

6. (Original) The organic EL panel according to claim 5, wherein

the gate length of the peripheral transistor is set to a value between 1 and 10 μm.

7. (Original) The organic EL panel according to claim 5, wherein

the gate length of the drive transistor is set to a value between 10 and 100 μm.

8. (Original) The organic EL panel according to claim 5, wherein

the gate width of the peripheral transistor is set to a value between 5 and 500 μm.

9. (Original) The organic EL panel according to claim 5, wherein

the gate width of the drive transistor is set to a value between 5 and 10 μm.